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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

ATTORNEY DOCKET NO. 035905-0118

Applicant: Igor G. KOUZNETSOV et al.

Title: TWO MASK FLOATING GATE EEPROM AND METHOD OF MAKING

Appl. No.: Unassigned

Filing Date: 02/05/2002

Examiner: Unassigned

Art Unit: Unassigned

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR §1.56

Commissioner for Patents
Washington, D.C. 20231

Sir:

Submitted herewith on Form PTO/SB/08B is a listing of documents known to Applicants in order to comply with Applicants' duty of disclosure pursuant to 37 CFR §1.56. A copy of each listed document is being submitted to comply with the provisions of 37 CFR §1.97 and §1.98.

The submission of any document herewith, which is not a statutory bar, is not intended as an admission that such document constitutes prior art against the claims of the present application or that such document is considered material to patentability as defined in 37 CFR §1.56(b). Applicants do not waive any rights to take any action which would be appropriate to antedate or otherwise remove as a competent reference any document which is determined to be a *prima facie* art reference against the claims of the present application.

TIMING OF THE DISCLOSURE

The listed documents are being submitted in compliance with 37 CFR §1.97(b), within three (3) months of the filing date of the application.

RELEVANCE OF EACH DOCUMENT

All of the documents are in English.

Applicants respectfully request that any listed document be considered by the Examiner and be made of record in the present application and that an initialed copy of Form PTO/SB/08B be returned in accordance with MPEP §609.

The Commissioner is hereby authorized to charge any additional fees which may be required regarding this application under 37 C.F.R. §§ 1.16-1.17, or credit any overpayment, to Deposit Account No. 19-0741. Should no proper payment be enclosed herewith, as by a check being in the wrong amount, unsigned, post-dated, otherwise improper or informal or even entirely missing, the Commissioner is authorized to charge the unpaid amount to Deposit Account No. 19-0741.

Respectfully submitted,

February 5, 2002
Date

for
Harold C. Wegner
Attorney for Applicant
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Sheet 1 of 7

Complete if Known	
Application Number	Unassigned
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Examiner Name	Unassigned
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JC828 U.S. PTO 10/063576 02/05/02

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	U.S. Patent Document Number	Kind Code[2] (*if known*)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	A1	5,427,979		Chang	06/27/1995	
	A2	5,070,384		McCollum et al.	12/03/1991	
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Attorney Docket Number	035905-0118

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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT				**Application Number**	Unassigned
				Filing Date	02/05/2002
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				Group Art Unit	Unassigned
(use as many sheets as necessary)				Examiner Name	Unassigned
Sheet	3	of	7	Attorney Docket Number	035905-0118

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[6]
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	A72	S.D. BROTHERTON et al.: "Excimer-Laser-Annealed Poly-Si Thin-Film Transistors," IEEE Transactions on Electron Devices, February 1993, pgs. 407-413, Vol. 40, No. 2, IEEE	
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	A121	DIETMAR GOGL et al.: "A 1-Kbit EEPROM in SIMOX Technology for High-Temperature Applications up to 250° C," IEEE Journal of Solid-State Circuits, October 2000, Vol. 35, No. 10, IEEE	
	A122	STANLEY WOLF: "Silicon Processing for the VLSI Era," Semiconductor Memory Process Integration, Volume 2	

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT				**Application Number**	Unassigned
				Filing Date	02/05/2002
Date Submitted: February 5, 2002				**First Nam d Inventor**	Igor KOUZNETSOV et al.
				Group Art Unit	Unassigned
(use as many sheets as necessary)				Examiner Name	Unassigned
Sheet	7	of	7	Attorney Docket Number	035905-0118

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No.[1]	U.S. Patent Document Number	Kind Code[2] (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Column, Lines, Where Relevant Passages or Relevant Figures Appear
	A123	5,383,149		Hong	01/17/1995	
	A124	5,572,046		Takemura	11/05/1996	

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	A125	WEB PAGE-ime.org.sg; "Tachyon and IME to Build 3D Chips for Greater Speed and Performance," Press Release, dated January 18, 2002	
	A126	ICHIRO FUJIWARA et al.: "MONOS Memory Cell Scalable to 0.1μm and Beyond," pages 117-118	

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